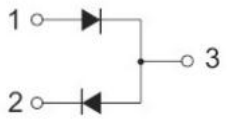
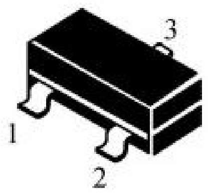
SOT-323 Switching Diode 开关二极管

■Internal Configuration 内部结构





■Features 特点

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Power dissipation 耗散功率	P_D(Ta=25℃)	200	mW
Forward Current 正向电流	I_F	150	mA
Non-Repetitive Peak Forward Current 不重复峰值正向电流	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms 不重复峰值正向浪涌电流	I_{FSM}	2000	mA
Reverse Voltage 反向电压	V_R	75	V
Thermal Resistance J-A 结到环境热阻	$R_{θJA}$	625	℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	-55to+150℃	

■Device Marking 产品打标

BAV99W=KJG

■Electrical Characteristics 电特性

(T$_A$=25℃ **unless otherwise noted** 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压(I_R=100uA)	$V_{(BR)}$	75	—	V
Reverse Leakage Current(V_R=25V) 反向漏电流(V_R=75V)	I_R	—	25 2.5	nA µA
Forward Voltage(I_F=1mA) 正向电压(I_F=10mA) (I_F=50mA) (I_F=150mA)	V_F	—	0.715 0.855 1.00 1.25	V
Diode Capacitance 二极管电容(V_R=0V, f=1MHz)	C_D	—	2	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	4	nS

■Typical Characteristic Curve 典型特性曲线

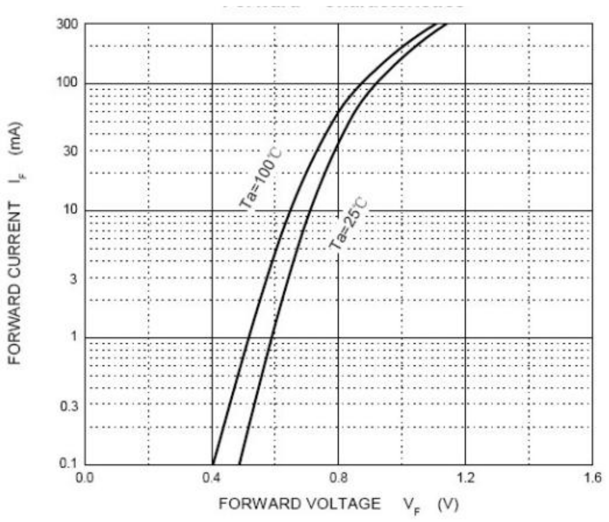


Figure 1: Forward Characteristics

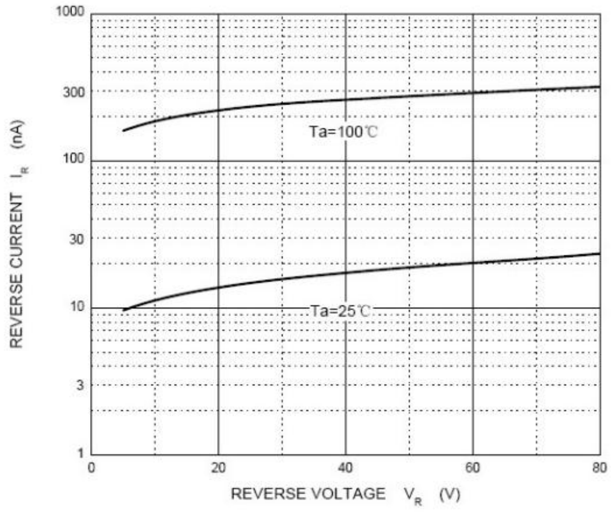


Figure 2: Leakage Current

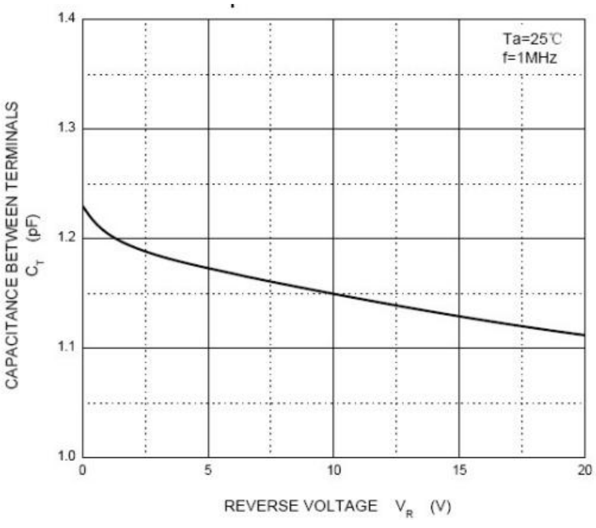


Figure 3: Capacitance Characteristics

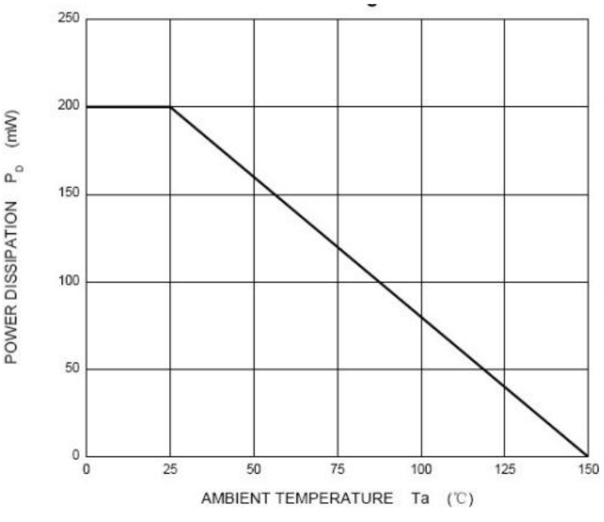
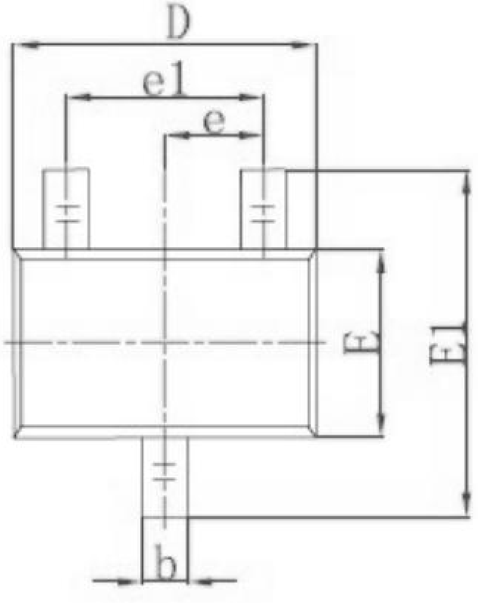
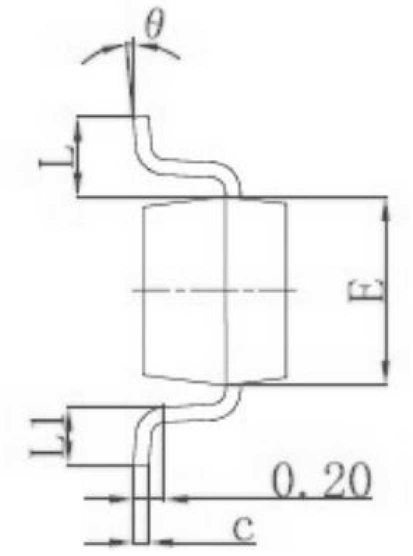
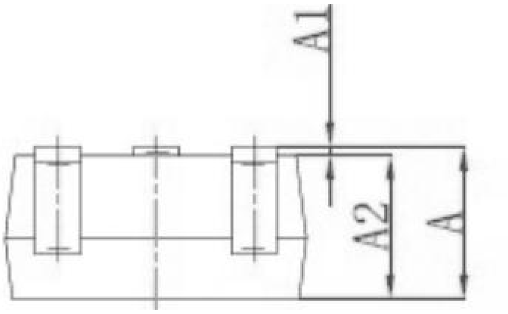


Figure 4：Power Derating Curve

■Dimension 外形封装尺寸







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°